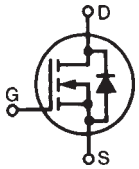
IXYS

PolarHV™ HiPerFET Power MOSFETs

IXFH 140N10P
IXFT 140N10P

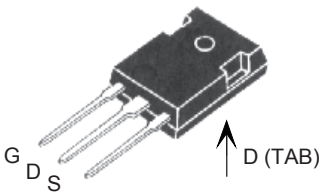
V_{DSS} = 100 V
I_{D25} = 140 A
$R_{DS(on)}$ ≤ 11 mΩ
t_{rr} ≤ 150 ns

N-Channel Enhancement Mode
Fast Intrinsic Diode
Avalanche Rated

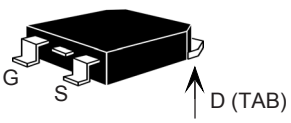


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	100	V
V_{DGR}	T_J = 25°C to 175°C; R_{GS} = 1 MΩ	100	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	140	A
$I_{D(RMS)}$	External lead current limit	75	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	300	A
I_{AR}	T_C = 25°C	60	A
E_{AR}	T_C = 25°C	80	mJ
E_{AS}	T_C = 25°C	2.5	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤100 A/μs, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$, R_G = 4 Ω	10	V/ns
P_D	T_C = 25°C	600	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6.0	g
	TO-268	5.0	g

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	100			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4.0 mA	3.0		5.0	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$			25	μA
	V_{GS} = 0 V, T_J = 175°C			500	μA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5\ I_{D25}$			11	mΩ
	V_{GS} = 15 V, I_D = 300 A, Note 1		9		mΩ

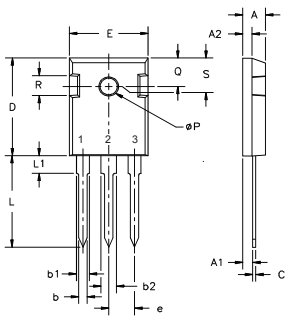
Symbol	Test Conditions	Characteristic Values (T_J = 25° C, unless otherwise specified) Min.	Typ.	Max.	
g_{fs}	V_{DS}= 10 V; I_D = 0.5 I_{D25}, Note 1	45	65		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4700		pF
C_{oss}			1850		pF
C_{rss}			600		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 60 A R_G = 4 Ω (External)		35		ns
t_r			50		ns
$t_{d(off)}$			85		ns
t_f			26		ns
$Q_{g(on)}$	V_{GS}= 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}		155		nC
Q_{gs}			33		nC
Q_{gd}			85		nC
R_{thJC}					0.25° C/W
R_{thCS}	(TO-247)		0.21		° C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25° C, unless otherwise specified) Min.	Typ.	Max.	
I_S	V_{GS} = 0 V			140	A
I_{SM}	Repetitive			300	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤300 μs, duty cycle d≤ 2 %			1.5	V
t_{rr}	I_F = 25 A, -di/dt = 100 A/μs		150	200	ns
Q_{RM}	V_R = 50 V, V_{GS} = 0 V		0.8		μC
I_{RM}			6		A

Note 1: Pulse test, t ≤300 μs, duty cycle d ≤ 2 %

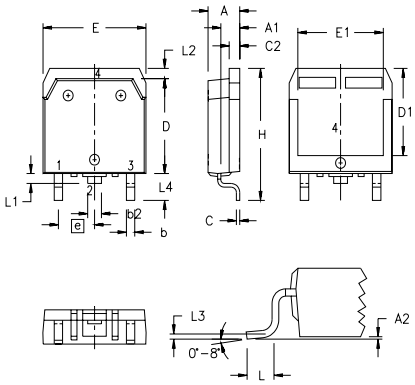
TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ 25ºC

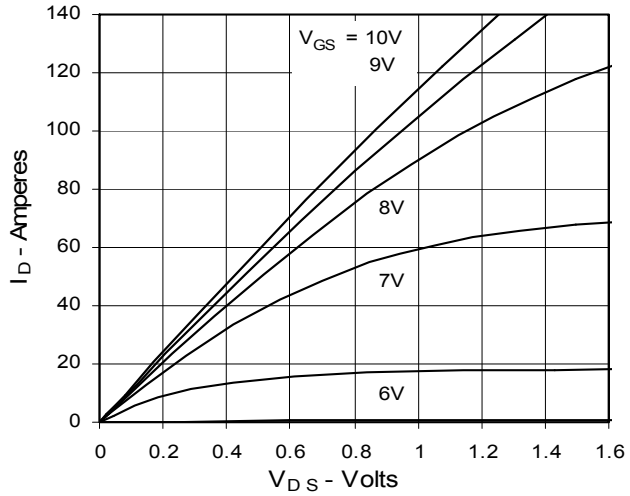


Fig. 2. Extended Output Characteristics @ 25ºC

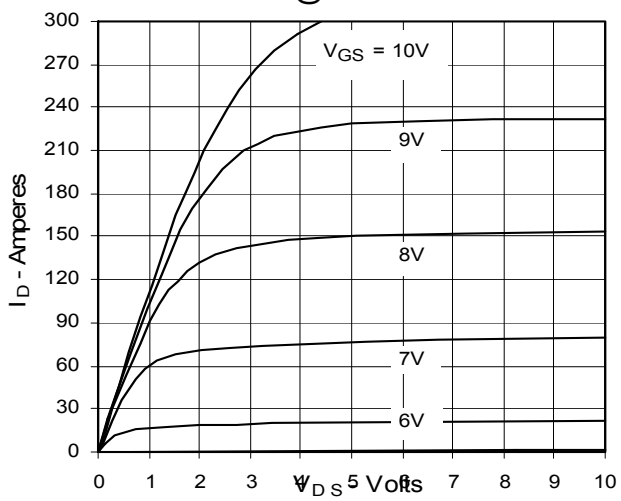


Fig. 3. Output Characteristics @ 150ºC

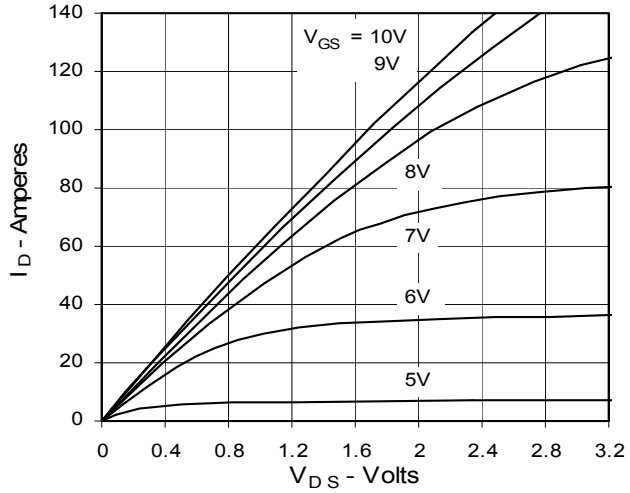


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

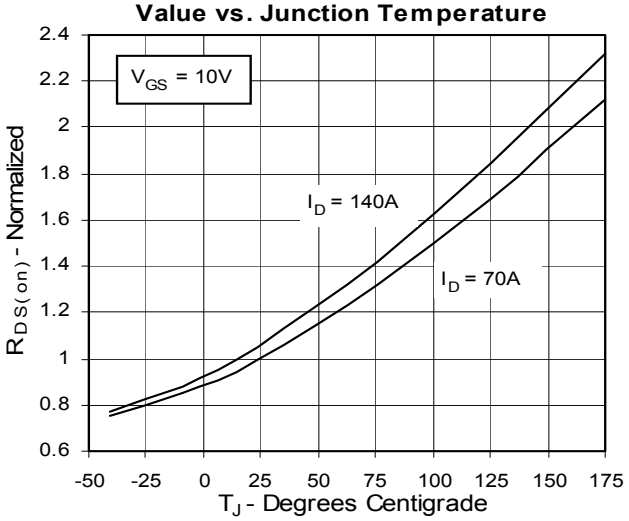


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Drain Current

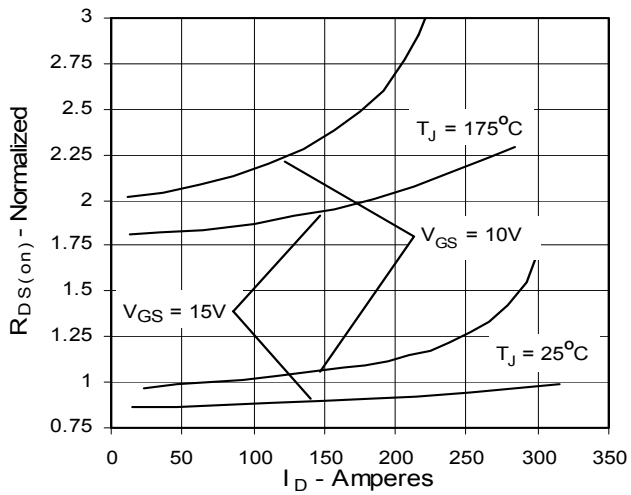


Fig. 6. Drain Current vs. Case Temperature

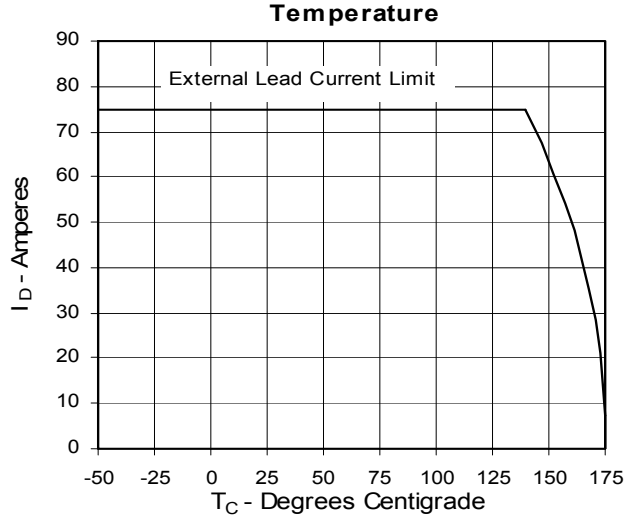


Fig. 7. Input Admittance

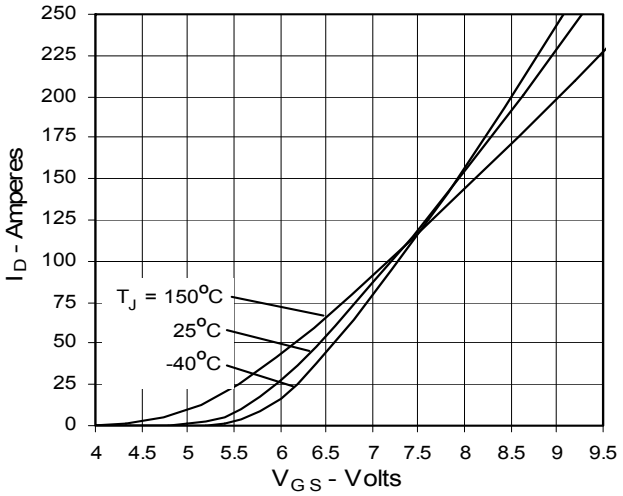


Fig. 8. Transconductance

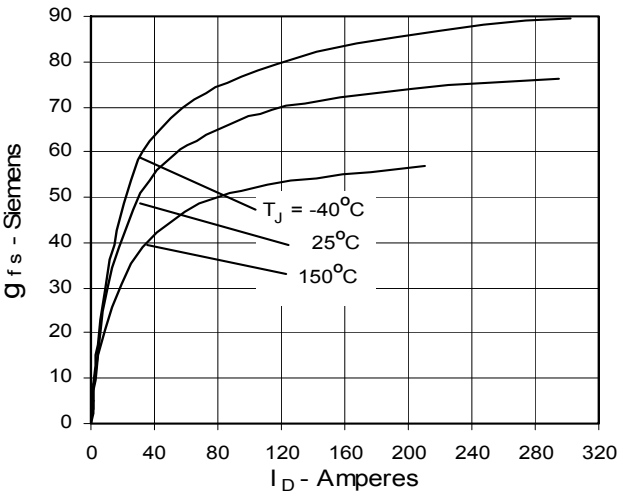


Fig. 9. Source Current vs. Source-To-Drain Voltage

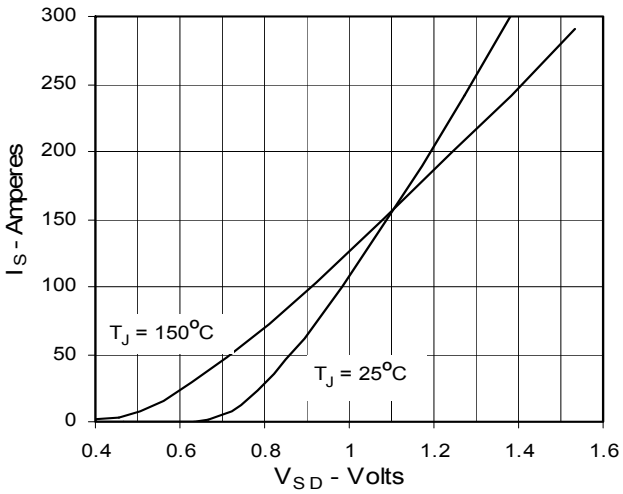


Fig. 10. Gate Charge

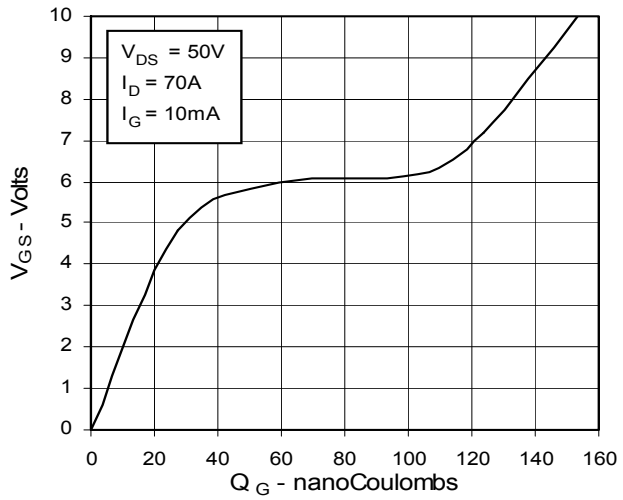


Fig. 11. Capacitance

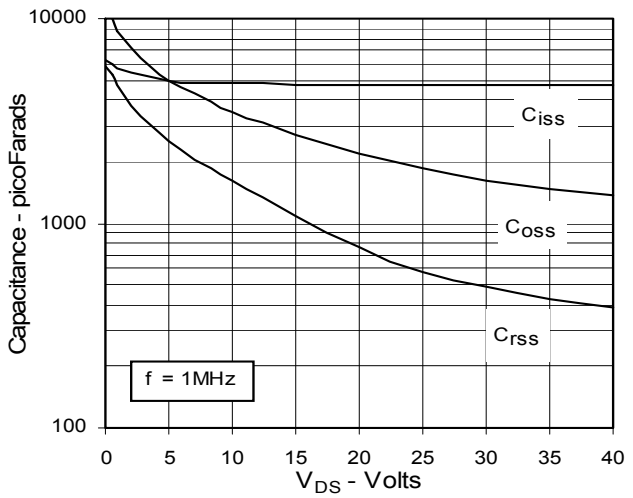


Fig. 12. Forward-Bias Safe Operating Area

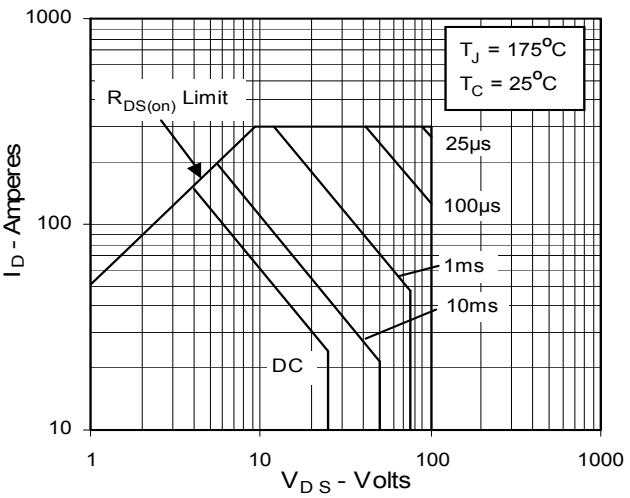


Fig. 13. Maximum Transient Thermal Resistance